

CHE323/CHE384
 Chemical Processes for Micro- and Nanofabrication
www.lithoguru.com/scientist/CHE323

Lecture 28

Device Interconnect, part 1

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Reading:
 Chapter 15, *Fabrication Engineering at the Micro- and Nanoscale*, 4th edition, Campbell

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Device Interconnect

- The CMOS process through transistor formation is called the front-end-of-line (FEOL)
- Connecting all of the transistors together with metal wires (called device interconnect or metallization) is the back-end-of-line (BEOL)
- As the number of transistors grew from thousands to billions, interconnect grew to become extremely difficult – a limitation to cost and performance of the IC

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Single-level Metallization

Legend:

- METAL1
- POLY
- CONTACT
- N DIFFUSION
- P DIFFUSION
- N-WELL

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Stick Diagram

Legend:

- N-diffusion
- P-diffusion
- Poly
- Metal

Poly used as local interconnect

Transistors share diffusion

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Metallization in Wiring Tracks

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Topology: Connecting Many Devices

Single level of metal

Multiple levels of metal

Place: where do I place the transistors?
 Route: where do I run the metal lines connecting them
 Goal: minimize length of wires and area of chip

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